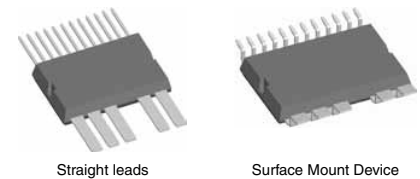
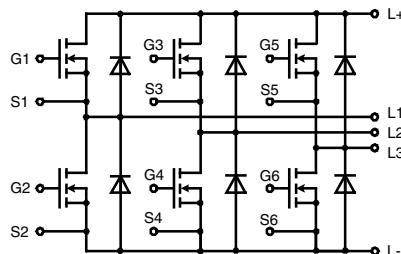


Three phase full Bridge with Trench MOSFETs in DCB isolated high current package

$$\begin{aligned} V_{DSS} &= 100 \text{ V} \\ I_{D25} &= 90 \text{ A} \\ R_{DSon \text{ typ.}} &= 7.5 \text{ m}\Omega \end{aligned}$$



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	100	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	90	A
I_{D90}	$T_C = 90^\circ\text{C}$	68	A
I_{F25}	$T_C = 25^\circ\text{C (diode)}$	90	A
I_{F90}	$T_C = 90^\circ\text{C (diode)}$	68	A

Applications

- AC drives
 - in automobiles
 - electric power steering
 - starter generator
 - in industrial vehicles
 - propulsion drives
 - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability 300 A max.
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Package options

- 2 lead frames available
 - straight leads (SL)
 - SMD lead version (SMD)

Symbol	Conditions	Characteristic Values			
		$(T_J = 25^\circ\text{C, unless otherwise specified})$			
		min.	typ.	max.	
$R_{DSon}^{1)}$	on chip level at $V_{GS} = 10 \text{ V}; I_D = 80 \text{ A}$		7.5	8.5	m Ω
			14		m Ω
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}; I_D = 250 \mu\text{A}$	2.5		4.5	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$		0.1	1	μA mA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2	μA
Q_g	$V_{GS} = 10 \text{ V}; V_{DS} = 65 \text{ V}; I_D = 90 \text{ A}$		90		nC
Q_{gs}			30		nC
Q_{gd}			30		nC
$t_{d(on)}$	inductive load $V_{GS} = 10 \text{ V}; V_{DS} = 48 \text{ V}$ $I_D = 70 \text{ A}; R_G = 33 \Omega;$ $T_J = 125^\circ\text{C}$		130		ns
t_r			95		ns
$t_{d(off)}$			290		ns
t_f			55		ns
E_{on}			0.4		mJ
E_{off}			0.4		mJ
$E_{rec off}$			0.007		mJ
R_{thJC}	with heat transfer paste (IXYS test setup)		1.3	1.0	K/W
R_{thJH}				1.6	K/W

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin \text{ to Chip}})$

Source-Drain Diode

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_{SD}	(diode) $I_F = 70 \text{ A}$; $V_{GS} = 0 \text{ V}$		0.9	1.2	V
t_{rr}	$I_F = 70 \text{ A}$; $-di_F/dt = 800 \text{ A}/\mu\text{s}$; $V_R = 48 \text{ V}$		55		ns
Q_{RM}			0.95		μC
I_{RM}			33		A

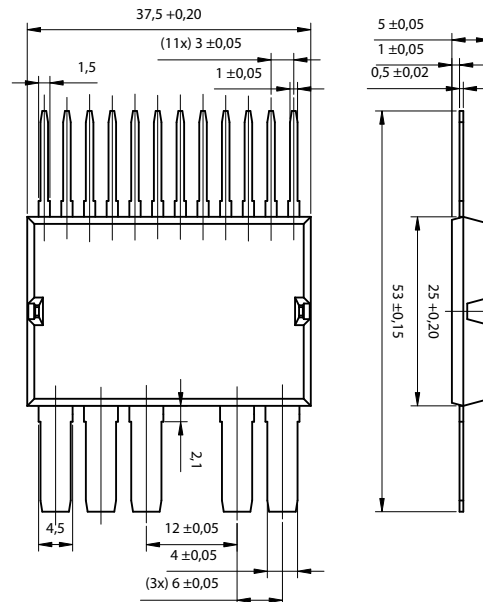
Component

Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections	300	A
T_J		-55...+175	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}$, 50/60 Hz, $f = 1 \text{ minute}$	1000	V~
F_C	mounting force with clip	50 - 250	N

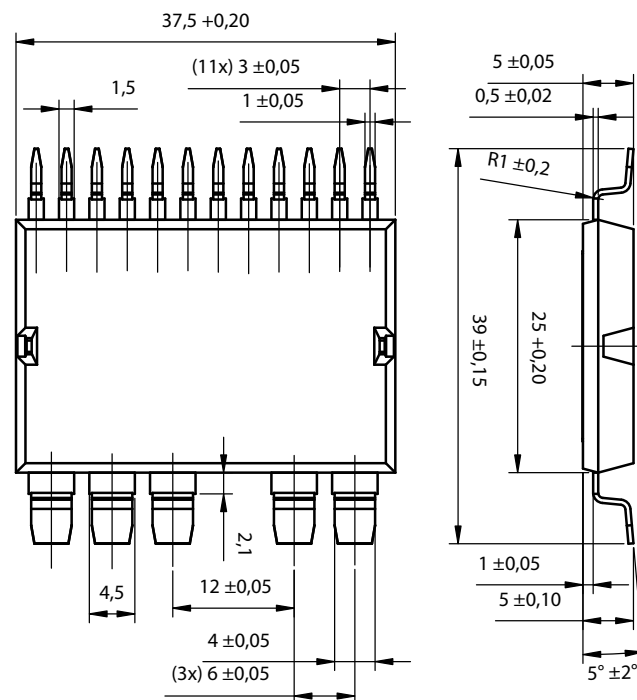
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
$R_{pin \text{ to chip}}^{1)}$			0.6		m Ω
C_P	coupling capacity between shorted pins and mounting tab in the case		160		pF
Weight			25		g

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + 2R_{Pin \text{ to Chip}})$

Straight Leads GWM 100-01X1-SL



Surface Mount Device GWM 100-01X1-SMD



Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
Straight	Standard	GWM 100-01X1 - SL	GWM 100-01X1	Blister	28	505 535
SMD	Standard	GWM 100-01X1 - SMD	GWM 100-01X1	Blister	28	505 542

IXYS reserves the right to change limits, test conditions and dimensions.

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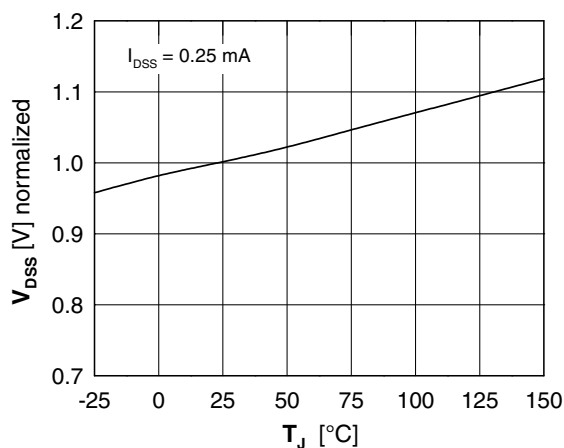


Fig. 1 Drain source breakdown voltage V_{DSS} vs. junction temperature T_J

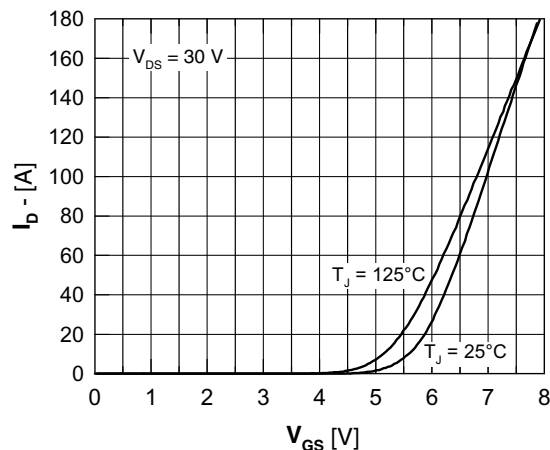


Fig. 2 Typical transfer characteristic

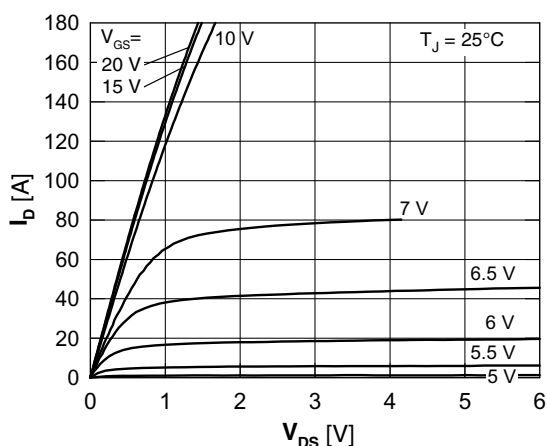


Fig. 3 Typical output characteristic

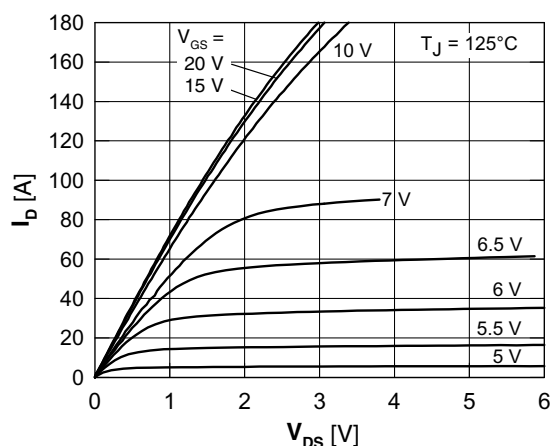


Fig. 4 Typical output characteristic

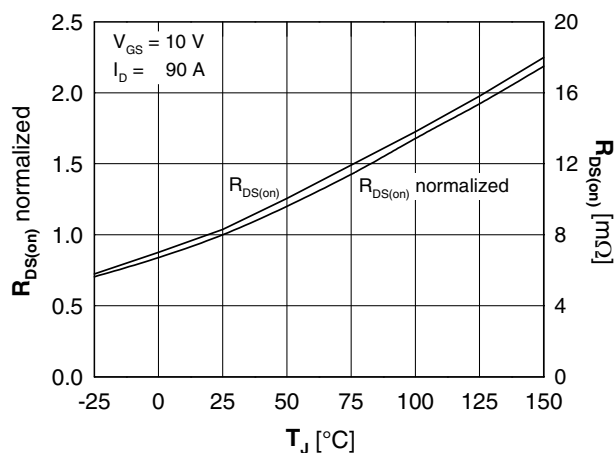


Fig. 5 Drain source on-state resistance $R_{DS(on)}$ versus junction temperature T_J

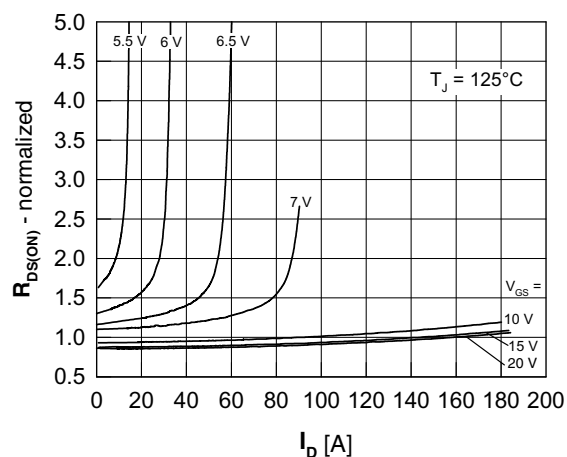


Fig. 6 Drain source on-state resistance $R_{DS(on)}$ versus I_D

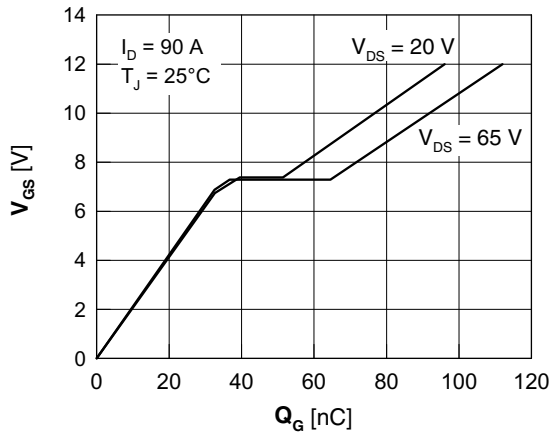


Fig. 7 Gate charge characteristic

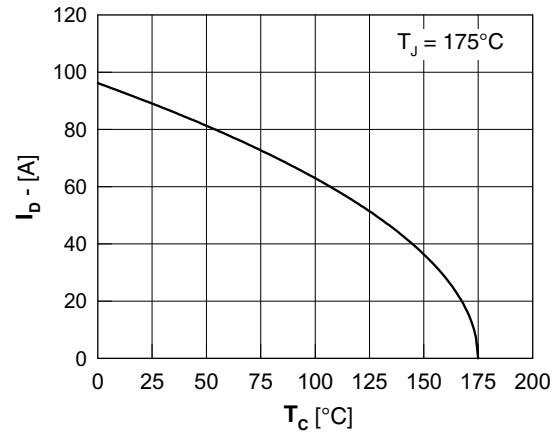


Fig. 8 Drain current I_D vs. case temperature T_C

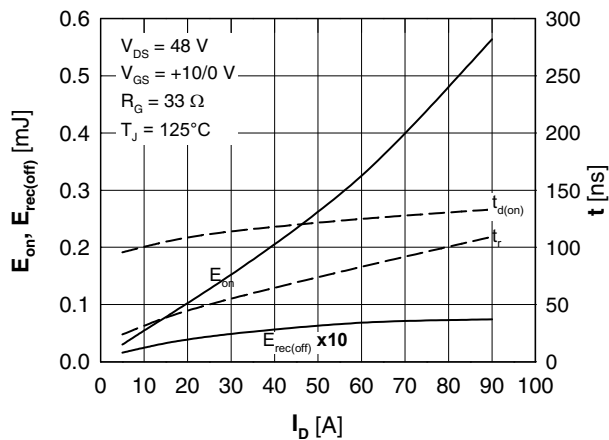


Fig. 9 Typ. turn-on energy & switching times vs. collector current, inductive switching

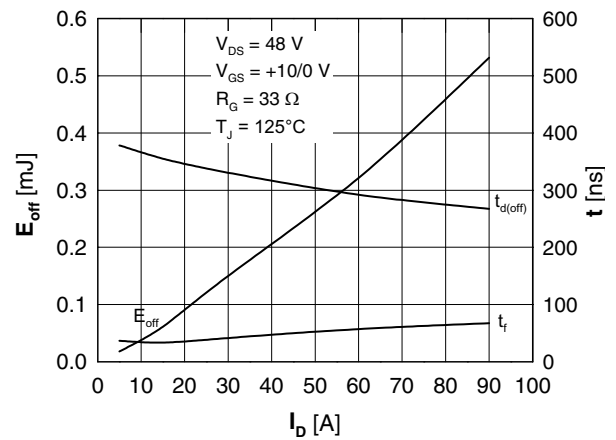


Fig. 10 Typ. turn-off energy & switching times vs. collector current, inductive switching

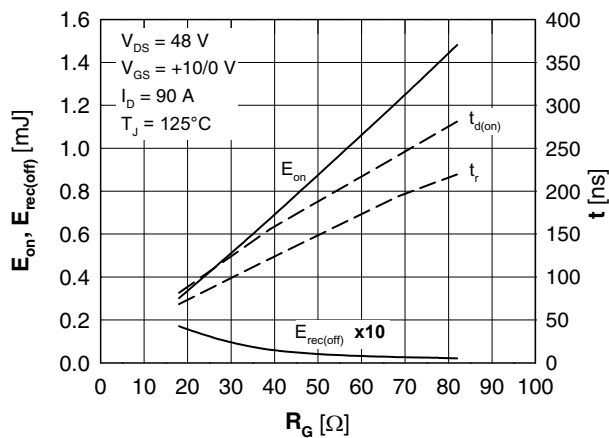


Fig. 11 Typ. turn-on energy & switching times vs. gate resistor, inductive switching

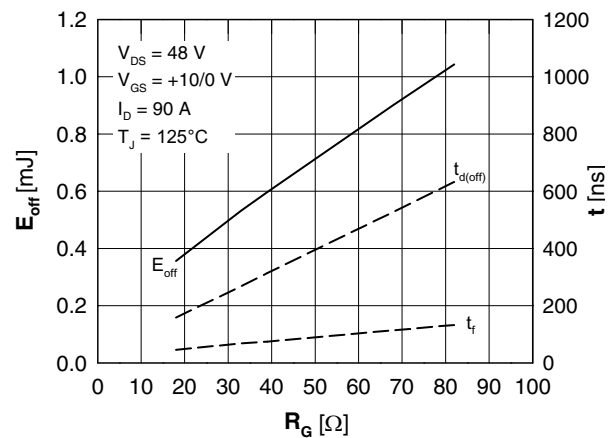


Fig. 12 Typ. turn-off energy & switching times vs. gate resistor, inductive switching

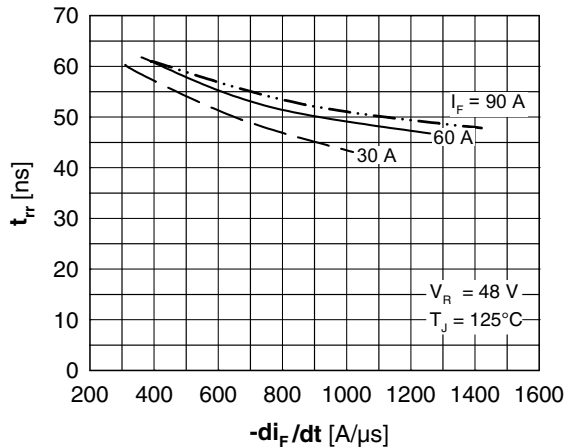


Fig. 13 Reverse recovery time t_{rr} of the body diode vs. di/dt

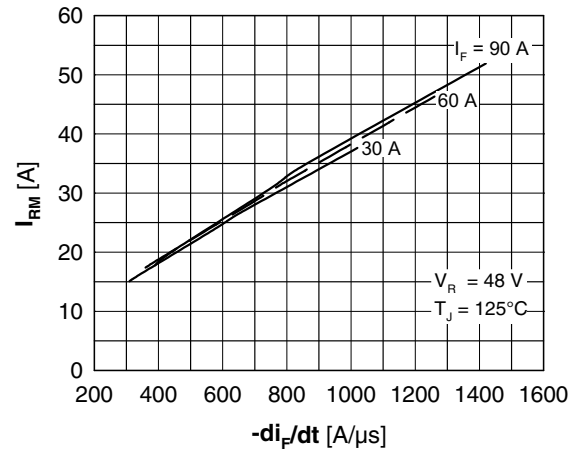


Fig. 14 Reverse recovery current I_{RM} of the body diode vs. di/dt

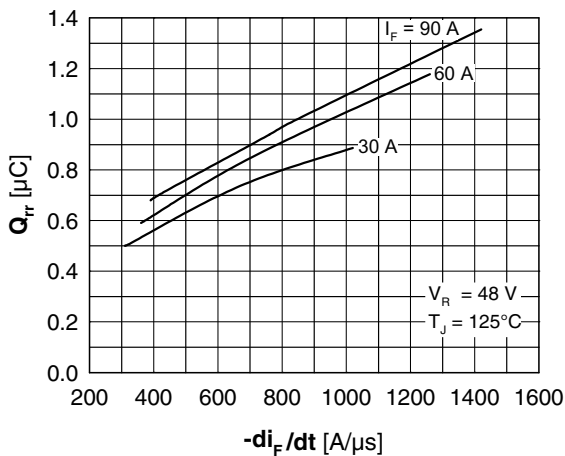


Fig. 15 Reverse recovery charge Q_{rr} of the body diode vs. di/dt

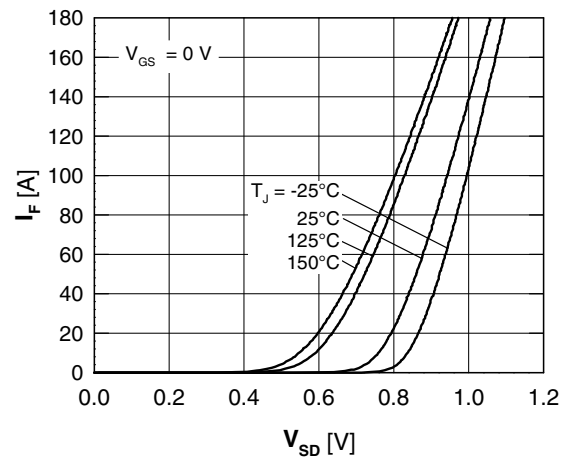


Fig. 16 Source drain diode current I_F vs. source drain voltage V_{SD} (body diode)

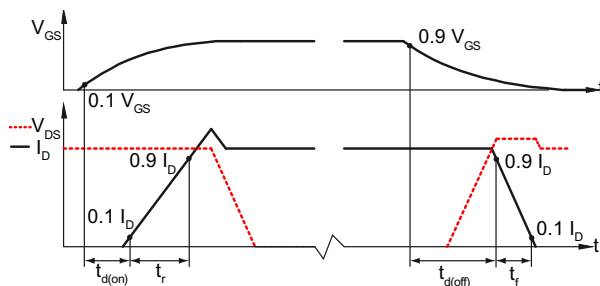


Fig. 17 Definition of switching times

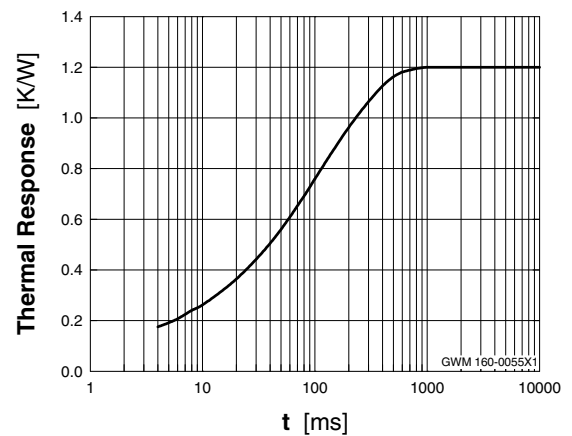


Fig. 18 Typ. thermal impedance junction to heatsink Z_{thJH} with heat transfer paste